

MXD8529A

0.1-3.0GHz SPDT Antenna Tuning Switch



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General Description

The MXD8529A is a CMOS silicon-on-insulator (SOI), single-pole, double-throw (SPDT) switch. The high linearity and ruggedness performance and extremely low insertion loss makes the device an ideal choice for GSM/WCDMA/LTE handset antenna tuning application.

The MXD8529A SPDT switch is provided in a compact 1.385mm x 1.485mm x 0.45mm 8-lead QFN package. A functional block diagram is shown in Figure 1. The pin configuration and package are shown in Figure 2. Signal pin assignments and functional pin descriptions are provided in Table 1.

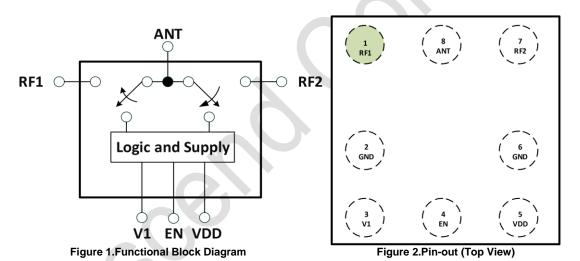
Applications

- GSM/WCDMA/LTE band and mode switching
- Antenna tuning switch

Features

- Broadband frequency range: 0.1 to 3.0 GHz
- Low insertion 0.30dB @ 2.7 GHz
- High P0.1dB of 43dBm
- Positive low voltage control: VC = 1.0 to 3.0 V,
 VDD = 2.5 to 3.0 V, Small, QFN (8-pin,
 1.385mm x 1.485mm x 0.45mm) package ,
 MSL1

Functional Block Diagram and Pin Function





Application Circuit

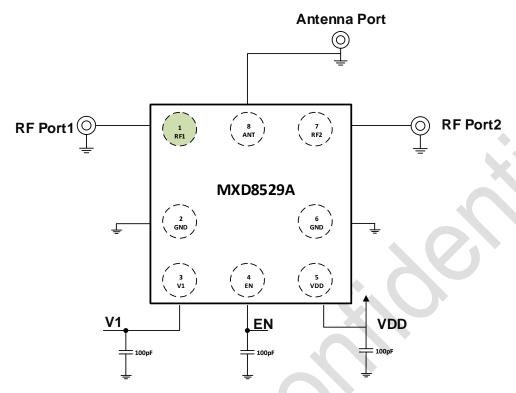


Figure 3. MXD8529A Application Circuit

Table 1. Pin Description

Pin No.	Name	Description	Pin No.	Name	Description
1	RF1	RF port 1	5	VDD	DC power supply
2	GND	Ground	6	GND	Ground
3	V1	DC control voltage	7	RF2	RF port 2
4	EN	DC control voltage	8	ANT	Antenna port

Truth Table

Table 2.

Active Path	EN	V1
ANT to RF1	1	0
ANT to RF2	1	1
OFF	0	1
Low Power Mode	0	0

Note: "1" = 1.0 V to 3.00 V. "0" = -0 V to +0.3 V.

Recommended Operation Range

Table 3.

Parameters	Symbol	Min	Тур	Max	Units
Operation Frequency	f1	0.1	-	3.0	GHz
Power supply	V_{DD}	2.5	2.8	3.0	٧
Switch Control Voltage High	V _{CTL_H}	1.0	1.8	3.0	٧
Switch Control Voltage Low	V _{CTL L}	0	0	0.3	٧



Specifications

Table 4.Electrical Specifications

Donomoton	Symbol	Specification		I I i i i a	Took Condition	
Parameter		Min.	Typical	Max.	Units	Test Condition
DC Specifications						
Control voltage:						
Low	V_{CTL_L}	0	0	0.3	V	
High	V _{CTL_H}	1.0	1.8	3.0	V	
Supply voltage	V_{DD}	2.5	2.8	3.0	V	
Supply current	I_{DD}		60		μA	$V_{DD} = 2.8 \text{ V}$
Control current	I _{CTL}		1		μA	V _{CTL} = 1.8 V
RF Specifications						
			0.20		dB	0.8 to 1.0 GHz
Insertion loss	IL		0.25		dB	1.0 to 2.2 GHz
			0.30		dB	2.2 to 3.0 GHz
		25	30		dB	0.8 to 1.0 GHz
Isolation	ISO	20	22		dB	1.0 to 2.2 GHz
		15	17		dB	2.2 to 3.0 GHz
Return loss	S ₁₁		22		dB	0.8 to 3.0 GHz
Input 0.1 dB compression point	P _{0.1dB}		+43		dBm	0.8 to 3.0 GHz, ANT to RF1 and RF2
Maximum RF operating voltage	V_{PK}		45	(V	25% duty cycle, OFF state, 0.8 to 3.0 GHz
On Resistance (RF1/2 to ANT)	Ron		1.3	1.4	Ω	Switch on Path
OFF Capacitance (RF1/2 to ANT)	Coff		140	160	fF	Switch off Path
Switching on time			2		μs	50% VCTL to 90% RF
Switching off time			2		μs	50% VCTL to 10% RF
Startup time			10		μs	Power off state to any RF switch state

Absolute Maximum Ratings

Table 5. Maximum ratings

Parameters	Symbol	Minimum	Maximum	Units
Supply voltage	V_{DD}	+2.5	+3.3	V
Digital control voltage	V_{CTL}	0	+3.0	V
RF input power	P _{IN}		+43.5	dBm
Operating temperature	T _{OP}	-35	+90	$^{\circ}$
Storage temperature	T _{STG}	-55	+150	$^{\circ}$
Peak RF operation voltage, 25% duty cycle, OFF state, f=700MHz to 2690MHz, V _{DD} =2.8V, V _{CTL} =1.8V	V _{RFPEAK}		50	V
Electrostatic Discharge Human body model (HBM), Class 1C	ESD_HBM		1000	
Machine Model (MM), Class A	ESD_MM		100	V
Charged device model (CDM), Class III	ESD_CDM		500	

Note: Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.



Package Outline Dimension

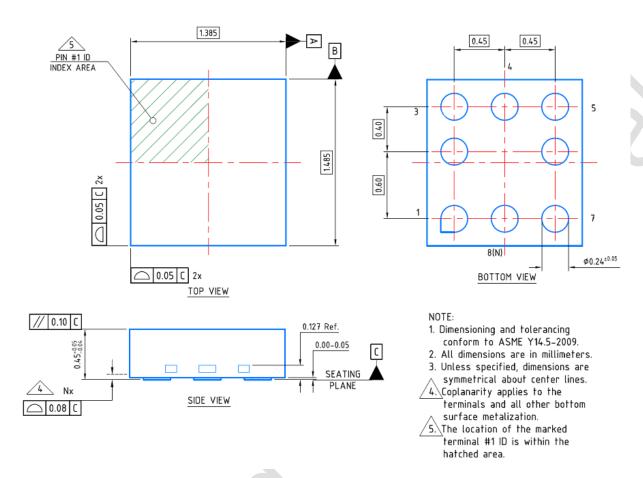


Figure 4. Package outline dimension



Marking Specification

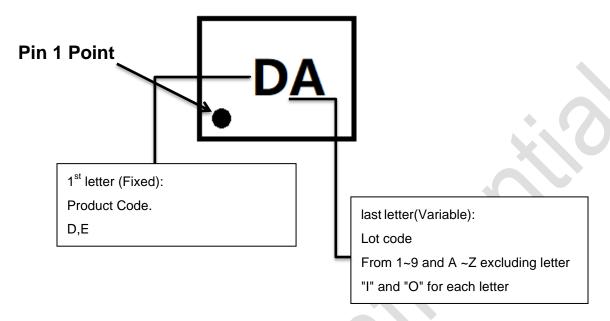


Figure 5. Marking specification (Top View)



Tape and Reel Dimensions

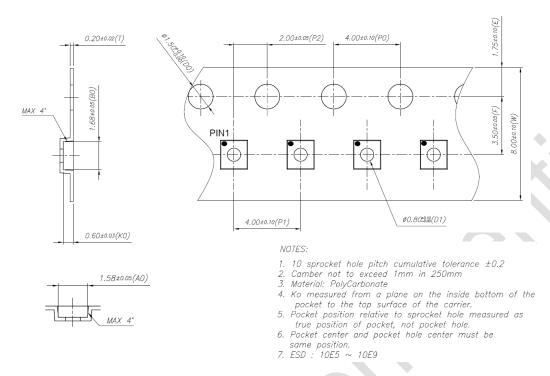


Figure 6. Tape and reel dimensions



Reflow Chart

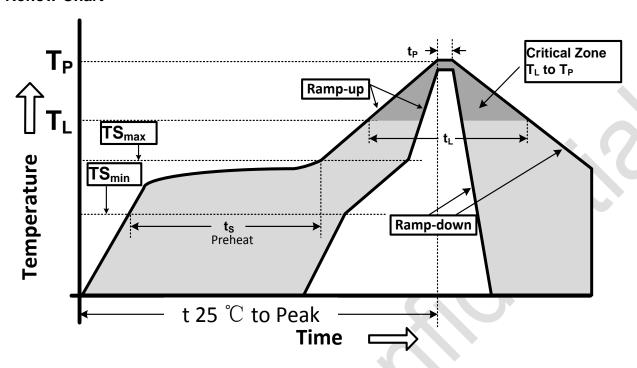


Figure 7. Recommended Lead-Free Reflow Profile

Table 6.

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection		
Ramp-up rate (TS _{max} to T _p)	3°C/second max.		
Preheat temperature (TS _{min} to TS _{max})	150°C to 200°C		
Preheat time (t _s)	60 - 180 seconds		
Time above TL , 217℃ (t _L)	60 - 150 seconds		
Peak temperature (T _p)	260℃		
Time within 5°C of peak temperature(t _p)	20 - 40 seconds		
Ramp-down rate	6°C/second max.		
Time 25°C to peak temperature	8 minutes max.		

ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.